PRODUCT SUMMARY

 $I_{T(AV)}$

110RKI...PbF, 111RKI...PbF Series

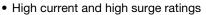
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Phase Control Thyristors (Stud Version), 110 A



110 A

FEATURES	
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· Hermetic ceramic housing

Thermetic ceramic mousing

ROHS

• Designed and qualified for industrial level

 Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		110	Α		
I _{T(AV)}	T _C	90	°C		
I _{T(RMS)}		172			
1	50 Hz	2080	Α		
ITSM	60 Hz	2180			
I ² t	50 Hz	21.7	kA ² s		
1-1	60 Hz	19.8	- KA-S		
V _{DRM} /V _{RRM}		400 to 1200	V		
t _q	Typical	110	μs		
T _J		- 40 to 140	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA				
	40	400	500					
110RKI 111RKI	80	800	900	20				
	120	1200	1300					



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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	ı	180° condu	ction, half sine v	NOVA	110	Α
at case temperature	I _{T(AV)}	100 Condu	Clion, nan sine v	wave	90	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 83 °C	case temperat	ure	172	
		t = 10 ms	No voltage		2080	
Maximum peak, one-cycle	,	t = 8.3 ms	reapplied		2180	А
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		1750	
		t = 8.3 ms reapplied	Sinusoidal half wave,	1830		
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	21.7	kA ² s
Manian 124 fau f	l ² t	t = 8.3 ms	reapplied		19.8	
Maximum I ² t for fusing	I-l	t = 10 ms	100 % V _{RRM}		15.3	KA-S
		t = 8.3 ms	reapplied		14.0	
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied		tage reapplied	217	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		0.82	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		1.02	V	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		2.16	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.70	11122	
Maximum on-state voltage	V_{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$		1.57	V	
Maximum holding current	I _H			V registive lead	200	A
Typical latching current	ΙL	T _J = 25 °C, anode supply 6 V resistive load 400		400	mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	300	A/μs		
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1			
Typical turn-off time	t _q	I_{TM} = 50 A, T_J = T_J maximum, dl/dt = - 5 A/ μ s V_R = 50 V, dV/dt = 20 V/ μ s, gate 0 V 25 Ω	110	– μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs		
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA		

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TRIGGERING						
PARAMETER	SYMBOL TEST CONDITIONS		CONDITIONS	VAL	UES	UNITS
PARAMETER	STINIBUL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	1	2	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	.0	VV
Maximum peak positive gate current	I _{GM}			3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms		0	V
Maximum peak negative gate voltage	- V _{GM}				10	
		T _J = - 40 °C	Maximum required gate trigger/current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		80	120	mA
		T _J = 140 °C		40	-	
		T _J = - 40 °C		2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C		1.6	2	٧
		T _J = 140 °C		1	-	1
DC gate current not to trigger	I _{GD}	T. T. maximum	Maximum gate current/ voltage not to trigger is the maximum value which will	6	.0	mA
DC gate voltage not to trigger	V _{GD}	ı ij= ijmaximum	$T_J = T_J$ maximum not trigger any unit with rated V_{DRM} anode to cathode applied		0.25	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		- 40 to 140	ۍ ت		
Maximum storage temperature range	T _{Stg}		- 40 to 150			
Maximum thermal resistance, junction to case		DC operation	0.27	K/W		
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.1	l v∧∧		
Mounting toyang 1100/		Non-lubricated threads	15.5 (137)	N · m		
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)		
Approximate weight			130	g		
Case style	se style See dimensions - link at the end of datashee		TO-209AC	(TO-94)		

△R _{thJC} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.043	0.031				
120°	0.052	0.053				
90°	0.066	0.071	$T_J = T_J \text{ maximum}$	K/W		
60°	0.096	0.101				
30°	0.167	0.169]			

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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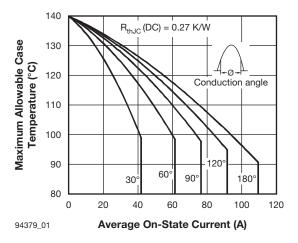


Fig. 1 - Current Ratings Characteristics

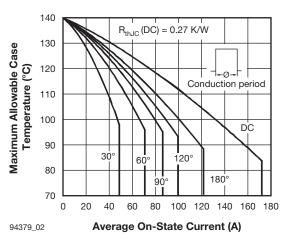
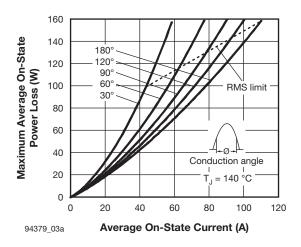


Fig. 2 - Current Ratings Characteristics



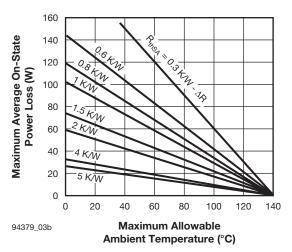
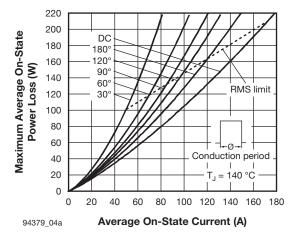


Fig. 3 - On-State Power Loss Characteristics



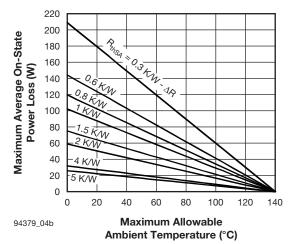


Fig. 4 - On-State Power Loss Characteristics

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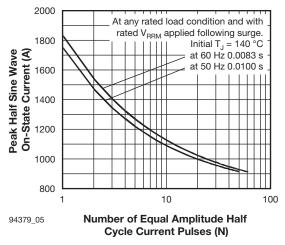


Fig. 5 - Maximum Non-Repetitive Surge Current

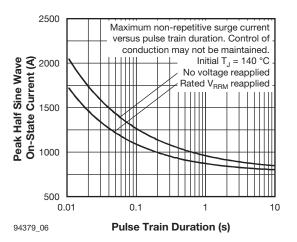


Fig. 6 - Maximum Non-Repetitive Surge Current

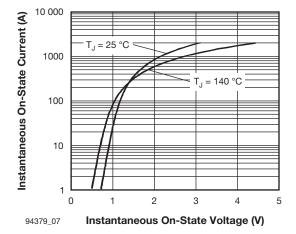


Fig. 7 - On-State Voltage Drop Characteristics

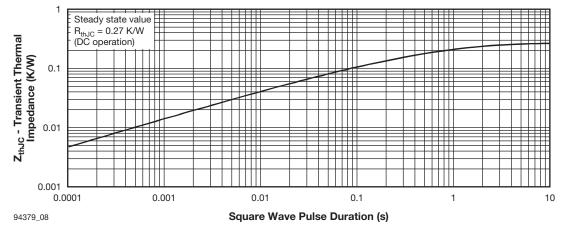


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

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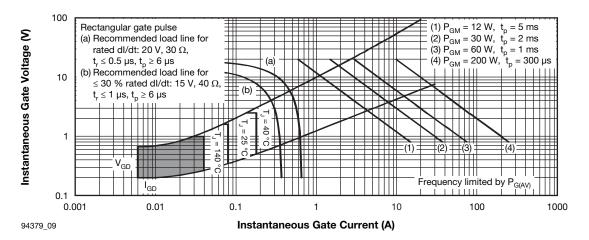
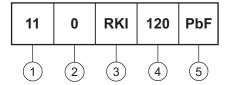


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 I_{T(AV)} rated average output current (rounded/10)
- 2 • 0 = Eyelet terminals (gate and auxiliary cathode leads)
 - 1 = Fast-on terminals (gate and auxiliary cathode leads)
- 3 Thyristor
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- None = Standard production
 - PbF = Lead (Pb)-free

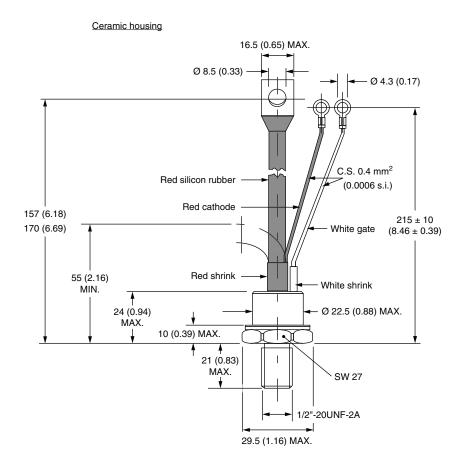
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95003			

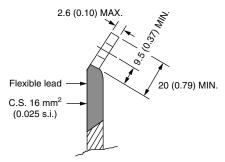


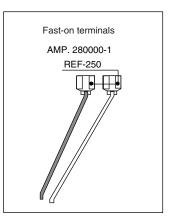
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TO-209AC (TO-94) for 110RKI and 111RKI Series

DIMENSIONS in millimeters (inches)







Note

• For metric device: M12 x 1.75 contact factory



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